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Brief Description of the Drawings

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The features and advantages of a semiconductor device according to the present invention and further details of a process of fabricating such a semiconductor device in accordance with the present invention will be more clearly understood from the following description taken in conjunction with the accompanying drawings in which like reference numerals designate similar or corresponding elements, regions and portions and in which:

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Figures 1, 2, 3A, 4, 5, 6, 7, 8, 9 and 10 are cross sectional views for illustrating a method for forming a capacitor and conductive lines according to an embodiment of the present invention.

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Figure 3B is a three dimensional view of the bottom plate with trenches according to an embodiment of the invention.